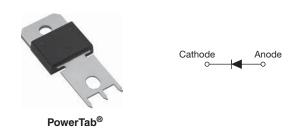
RoHS COMPLIANT



## Vishay Semiconductors

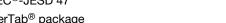
# Ultrafast Soft Recovery Diode, 150 A FRED Pt®

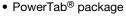


PRODUCT SUMMARY				
Package	PowerTab <sup>®</sup>			
I <sub>F(AV)</sub>	150 A			
$V_{R}$	200 V			
V <sub>F</sub> at I <sub>F</sub>	0.79 V			
t <sub>rr</sub> (typ.)	See recovery table			
T <sub>J</sub> max.	175 °C			
Diode variation	Single die			

#### **FEATURES**

- · Ultrafast recovery time
- 175 °C max. operating junction temperature
- Screw mounting only
- Designed and qualified according to JEDEC®-JESD 47





 Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>



- Reduced RFI and EMI
- Higher frequency operation
- · Reduced snubbing
- · Reduced parts count

#### **DESCRIPTION / APPLICATIONS**

These diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems.

The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for HF welding, power converters and other applications where switching losses are not significant portion of the total losses.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS	
Cathode to anode voltage	$V_R$		200	V	
Continuous forward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 116 °C	150		
Single pulse forward current	I <sub>FSM</sub>	T <sub>C</sub> = 25 °C	1600	Α	
Maximum repetitive forward current	I <sub>FRM</sub>	Square wave, 20 kHz	380		
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C	

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	$V_{BR}$ , $V_{R}$ $I_{R} = 100 \mu A$		200	-	-	
Forward voltage V <sub>F</sub>	V	I <sub>F</sub> = 150 A	-	0.99	1.13	V
	٧F	I <sub>F</sub> = 150 A, T <sub>J</sub> = 175 °C	-	0.79	0.90	
Reverse leakage current I <sub>R</sub>		$V_R = V_R$ rated	-	-	50	μA
	T <sub>J</sub> = 150 °C, V <sub>R</sub> = V <sub>R</sub> rated	-	-	2	mA	
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 200 V	-	180	-	pF
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	3.5	-	nH



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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		I <sub>F</sub> = 1.0 A, dI <sub>F</sub> /dt =	200 A/μs, V <sub>R</sub> = 30 V	-	-	45	
Reverse recovery time	e recovery time t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	34	-	ns
		T <sub>J</sub> = 125 °C		-	58	-	
Peak recovery current I <sub>RRM</sub>	T <sub>J</sub> = 25 °C	$I_F = 150 \text{ A}$ $V_R = 160 \text{ V}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$	-	4.5	-	Α	
	T <sub>J</sub> = 125 °C		-	9.0	-		
Reverse recovery charge Q <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	87	=	nC	
	T <sub>J</sub> = 125 °C		-	300	=		

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Thermal resistance, junction to case	R <sub>thJC</sub>		=	-	0.35	K/W
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	0.2	-	T N/VV
Weight			-	-	5.02	g
vveignt			-	0.18	-	oz.
Mounting torque			1.2	_	2.4	N·m
meaning to que			(10)		(20)	(lbf · in)
Marking device		Case style PowerTab®	150EBU02			

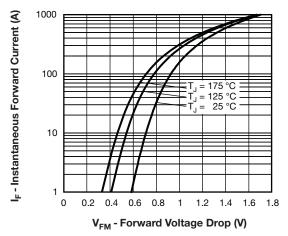


Fig. 1 - Maximum Forward Voltage Drop Characteristics

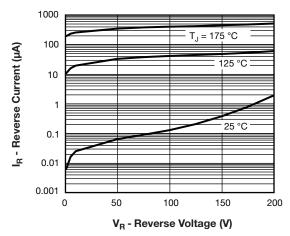


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

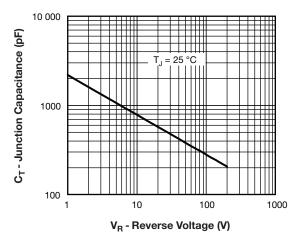


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

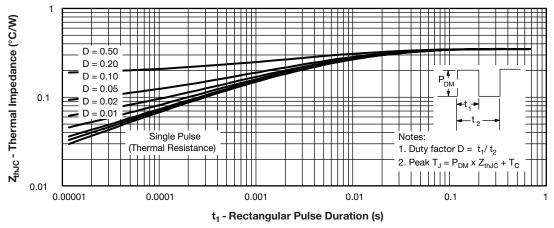


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

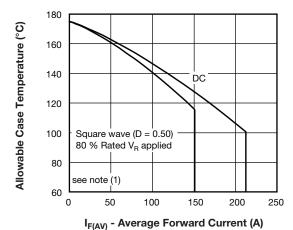


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

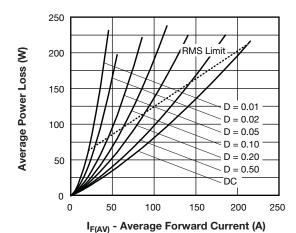


Fig. 6 - Forward Power Loss Characteristics



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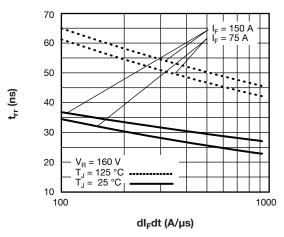


Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

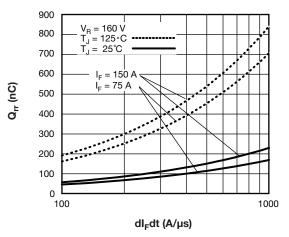


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt

#### Note

(1) Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ;  $Pd = Forward power loss = I_{F(AV)} \times V_{FM}$  at  $(I_{F(AV)}/D)$  (see fig. 6);  $Pd_{REV} = Inverse power loss = V_{R1} \times I_R (1 - D)$ ;  $I_R$  at  $V_{R1} = 80 \%$  rated  $V_R$ 

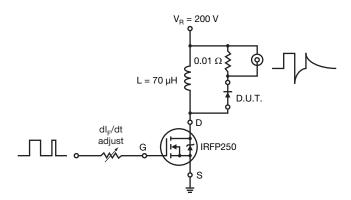
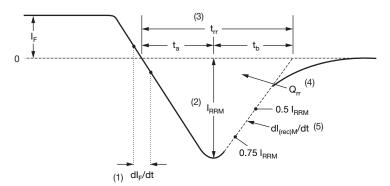


Fig. 9 - Reverse Recovery Parameter Test Circuit

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- (1) dl<sub>F</sub>/dt rate of change of current through zero crossing
- (2) I<sub>RRM</sub> peak reverse recovery current
- (3) t<sub>rr</sub> reverse recovery time measured from zero crossing point of negative going I<sub>F</sub> to point where a line passing through 0.75 I<sub>RRM</sub> and 0.50 I<sub>RRM</sub> extrapolated to zero current.
- (4)  $Q_{rr}$  area under curve defined by  $t_{rr}$  and  $I_{RRM}$

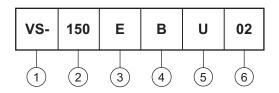
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) dI<sub>(rec)M</sub>/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 10 - Reverse Recovery Waveform and Definitions

#### **ORDERING INFORMATION TABLE**

**Device code** 



- Vishay Semiconductors product
- 2 Current rating (150 = 150 A)
- 3 Single diode
- 4 PowerTab<sup>®</sup> (ultrafast/hyperfast only)
- 5 Ultrafast recovery
- 6 Voltage rating (02 = 200 V)

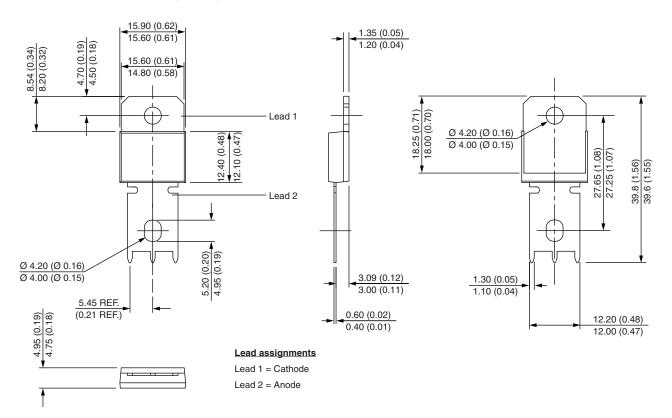
LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95240				
Part marking information	www.vishay.com/doc?95370				
Application note	www.vishay.com/doc?95179				



### Vishay Semiconductors

### PowerTab<sup>®</sup>

#### **DIMENSIONS** in millimeters (inches)





### **Legal Disclaimer Notice**

Vishay

#### **Disclaimer**

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